
2SK2595

Silicon N-Channel MOS FET
UHF Power Amplifier

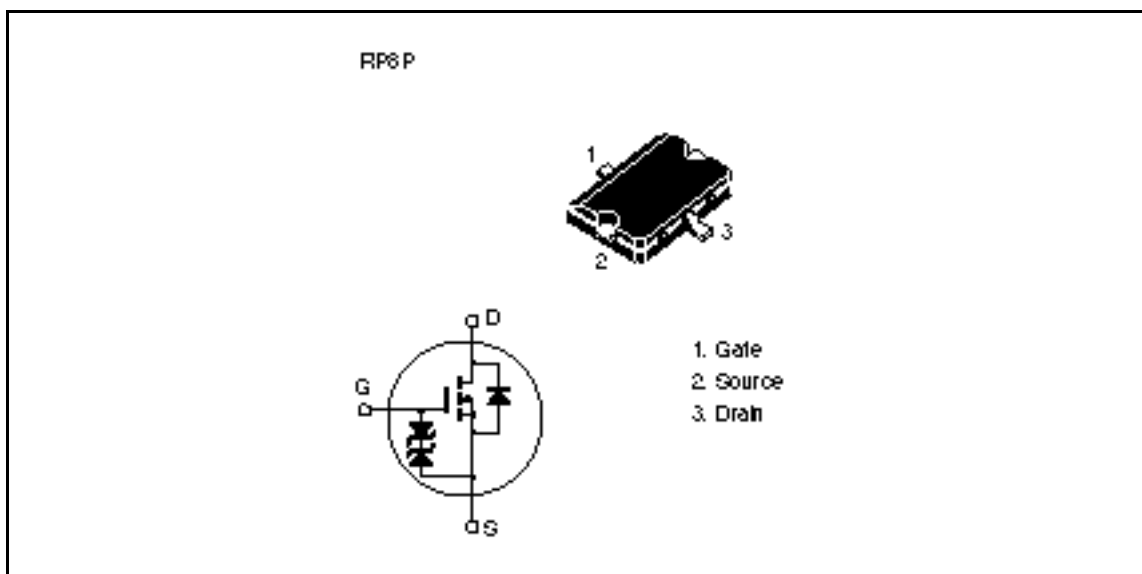
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1st. Edition

Features

- High power output, High gain, High efficiency
PG = 7.8dB, Pout = 37.3dBm, D = 50 % min. (f = 836.5MHz)
- Compact package capable of surface mounting

Outline



This Device is sensitive to Electro Static Discharge.
An Adequate handling procedure is requested.

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Absolute Maximum Ratings (Ta = 25°C)

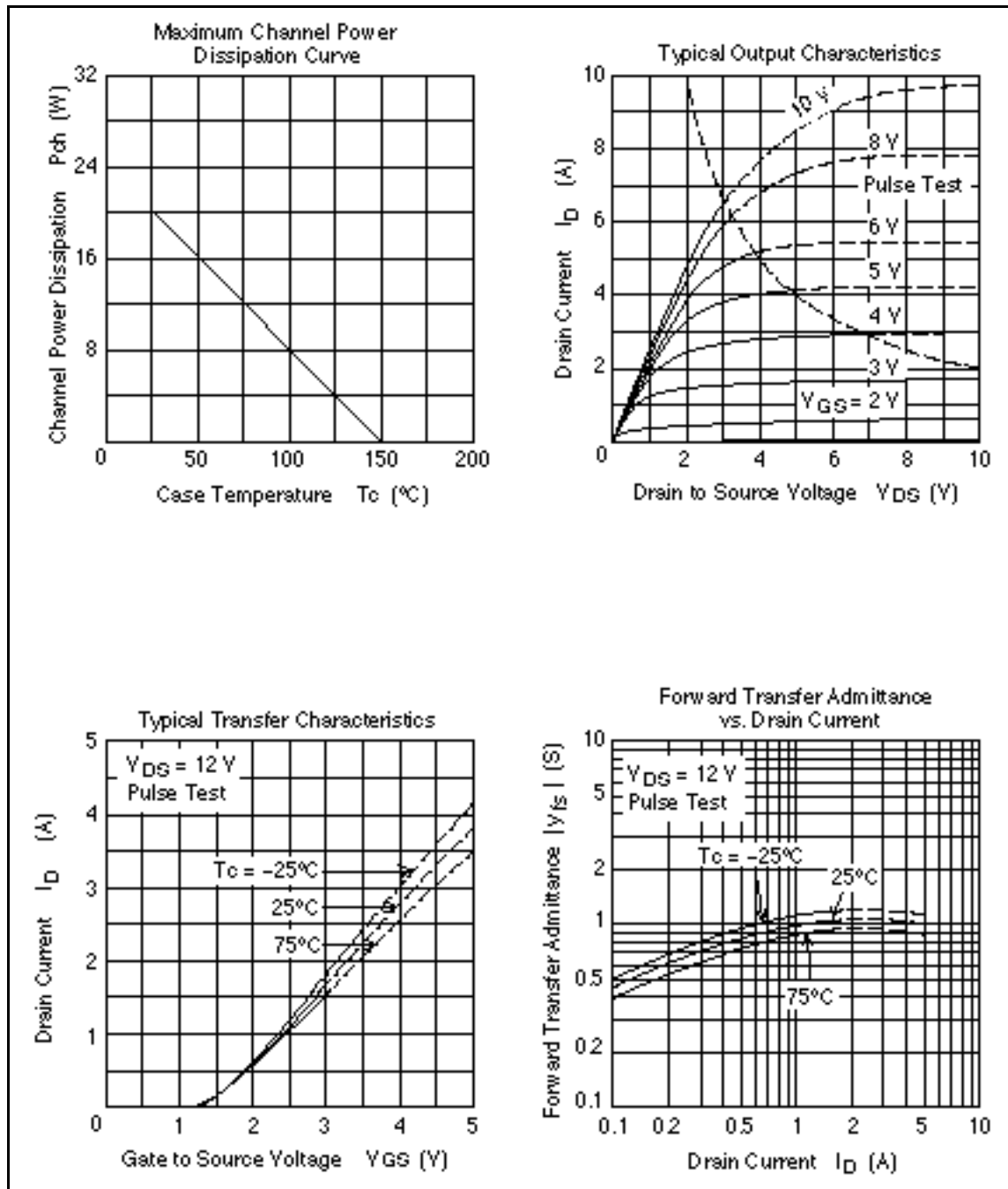
Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	17	V
Gate to source voltage	V _{GSS}	±10	V
Drain current	I _D	1.1	A
Drain peak current	I _{D(pulse)} *1	5	A
Channel dissipation	Pch*2	20	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-45 to +150	°C

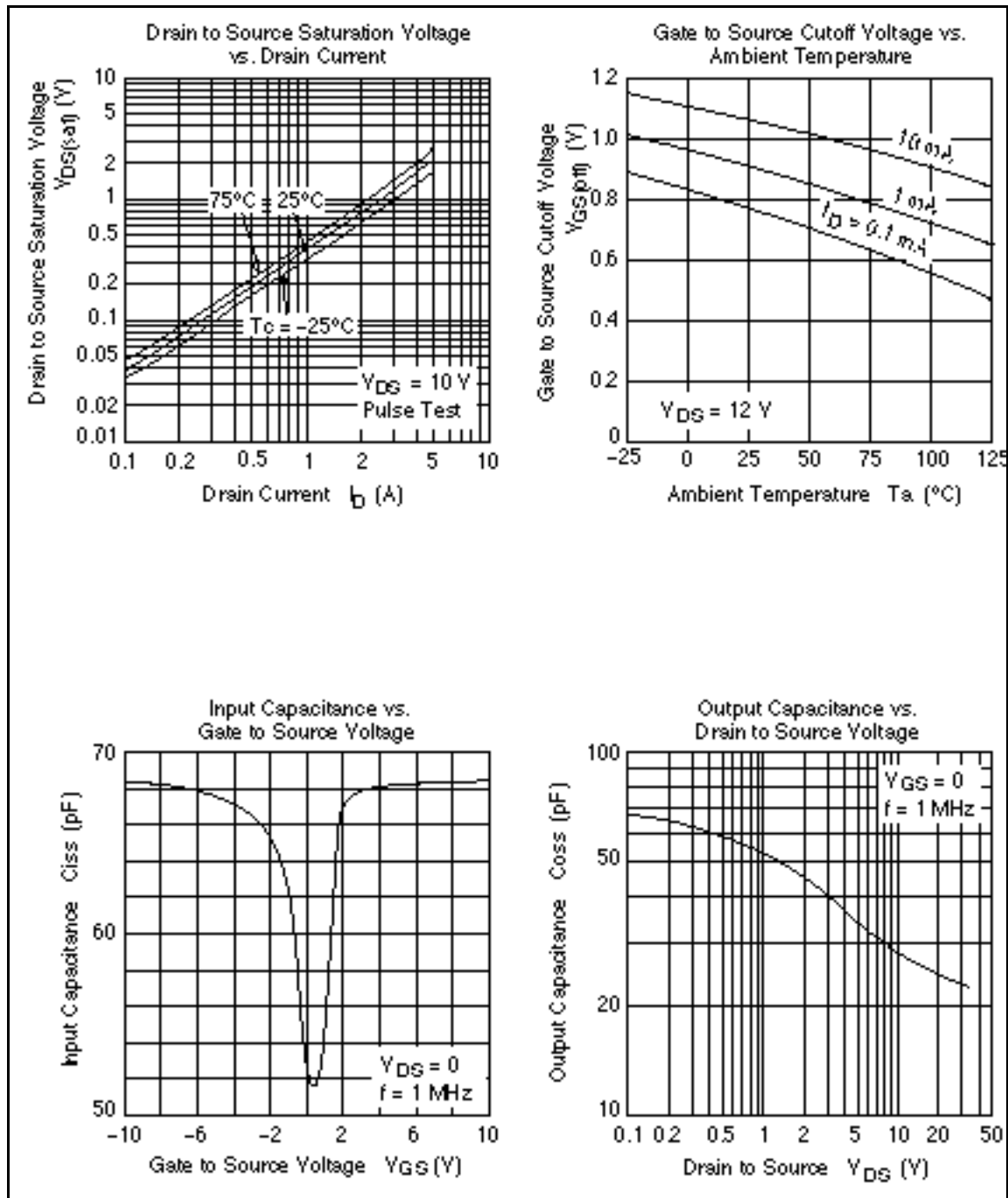
Notes: 1. PW = 10μs, duty cycle = 1 %
2. Value at Tc = 25°C

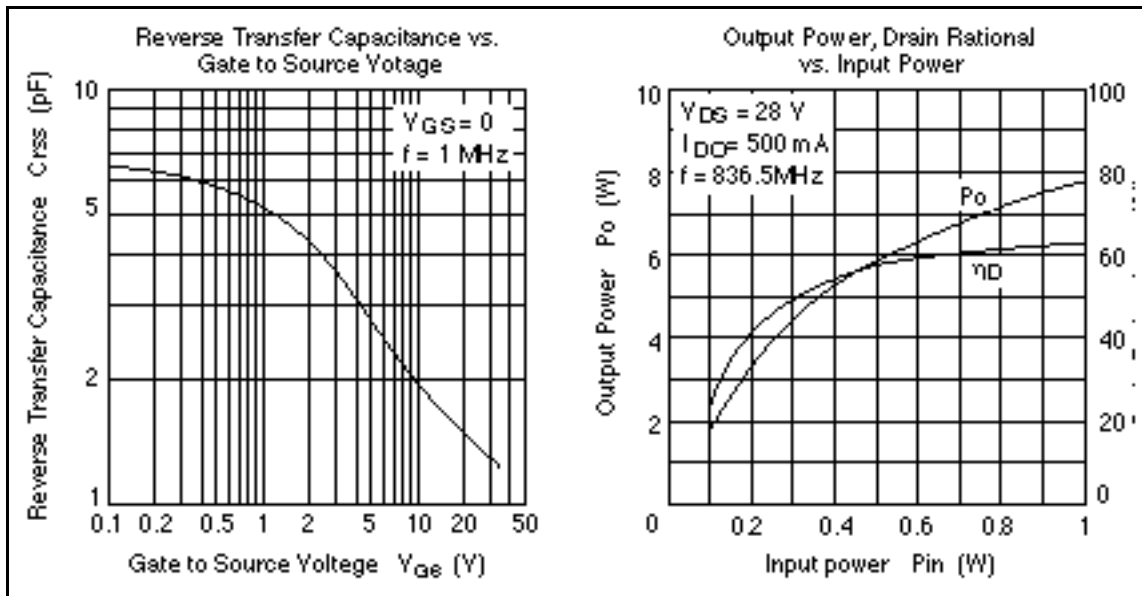
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min.	Typ	Max.	Unit	Test Conditions
Zero gate voltage drain current	I _{DSS}	—	—	10	μA	V _{DS} = 12 V, V _{GS} = 0
Gate to source leak current	I _{GSS}	—	—	±5.0	μA	V _{GS} = ±10V, V _{DS} = 0
Gate to source cutoff voltage	V _{GS(off)}	0.6	—	1.3	V	I _D = 6mA, V _{DS} = 12V
Input capacitance	Ciss	—	68	—	pF	V _{GS} = 5V, V _{DS} = 0 f = 1MHz
Output capacitance	Coss	—	27	—	pF	V _{DS} = 12V, V _{GS} = 0 f = 1MHz
Output Power	Pout	37.3	38.45	—	dBm	V _{DS} = 12V, f = 836.5MHz Pin = 29.5dBm
Drain Rational	D	50	60	—	%	V _{DS} = 12V Pout = 37.3dBm f = 836.5MHz Pin = 29.5dBm

Main Characteristics



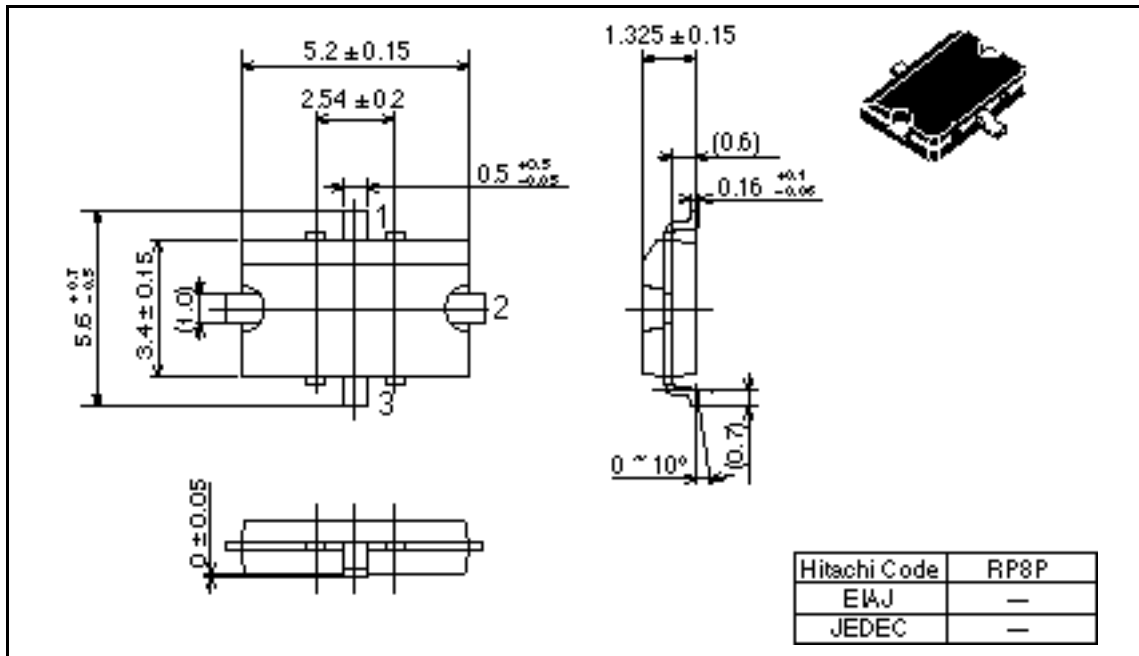




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Package Dimensions

Unit: mm



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